

LIGHT-EMITTING DEVICE

Abstract

The present invention discloses a light-emitting device that has a substrate, an n-type electrode, an active layer, a p-type semiconductor layer, a reflective layer, and a p-type electrode. The n-type electrode is located on the bottom surface of the substrate and the active layer is located on a top surface of the substrate. The p-type semiconductor layer covers the active layer. The reflective layer is located on the p-type semiconductor layer, and the p-type electrode covers the reflective layer. The reflective layer is a conductive layer with high reflectivity, and is formed under the p-type electrode to avoid light of the light-emitting device being absorbed by the metal electrode.